

CLAIMS

What is claimed is:

1 1. A method of processing for a semiconductor device,
2 the method comprising:
3 providing a wafer including a substrate;
4 forming a plurality of sidewalls around a plurality of
5 cylindrical pedestals above a surface of the substrate;
6 removing the plurality of cylindrical pedestals; and
7 vertically etching horizontal surfaces of a first
8 material located around the plurality of sidewalls.

1 2. The method of claim 1, wherein,
2 the plurality of sidewalls provide an etch stop.

1 3. The method of claim 2, wherein,
2 the plurality of sidewalls protect the first material
3 under the plurality of sidewalls from being etched during the
4 vertical etching of the first material.

1 4. The method of claim 1, further comprising:
2 removing the plurality of sidewalls.

1 5. The method of claim 1, further comprising:
2 diffusing a dopant into the first material located
3 around the plurality of sidewalls.

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1 6. The method of claim 1, further comprising:
2 diffusing a dopant into a second material around the
3 plurality of sidewalls.

1 7. The method of claim 1, further comprising:
2 diffusing a dopant into the first material and a second
3 material around the plurality of sidewalls.

1 8. The method of claim 1, further comprising:
2 diffusing a dopant into the first material or a second
3 material around the plurality of sidewalls.

1 9. The method of claim 8, wherein,
2 the plurality of sidewalls provide an etch stop and a
3 diffusion barrier.

1 10. The method of claim 9, wherein,
2 the plurality of sidewalls protect the first material
3 under the plurality of sidewalls from receiving a dopant
4 during the diffusing of the dopant into the first material or
5 the second material.

1 11. The method of claim 9, wherein,
2 the plurality of sidewalls protect the second material
3 under the plurality of sidewalls from receiving a dopant

4 during the diffusing of the dopant into the first material
5 and the second material.

1 12. The method of claim 9, wherein,
2 the plurality of sidewalls protect the first material
3 and the second material under the plurality of sidewalls from
4 receiving a dopant during the diffusing of the dopant into
5 the first material or the second material.

1 13. A method of processing for a semiconductor device,
2 the method comprising:
3 providing a wafer including a substrate;
4 forming a plurality of sidewalls around a plurality of
5 cylindrical pedestals above a surface of the substrate;
6 removing the plurality of cylindrical pedestals; and
7 diffusing a dopant into a first material located around
8 the plurality of sidewalls.

1 14. The method of claim 13, wherein,
2 the plurality of sidewalls provide a diffusion barrier.

1 15. The method of claim 14, wherein,
2 the plurality of sidewalls protect the first material
3 under the plurality of sidewalls from receiving a dopant
4 during the diffusing of the dopant into the first material.

1 16. The method of claim 13, further comprising:

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2 removing the plurality of sidewalls.

1 17. The method of claim 13, further comprising:

2 vertically etching horizontal surfaces of the first
3 material located around the plurality of sidewalls.

1 18. The method of claim 13, further comprising:

2 vertically etching horizontal surfaces of a second
3 material located around the plurality of sidewalls.

1 19. The method of claim 13, further comprising:

2 vertically etching horizontal surfaces of the first
3 material and a second material located around the plurality
4 of sidewalls.

1 20. The method of claim 13, further comprising:

2 vertically etching horizontal surfaces of the substrate
3 located around the plurality of sidewalls.

1 21. The method of claim 13, further comprising:

2 vertically etching horizontal surfaces of the first
3 material or a second material located around the plurality of
4 sidewalls.

1 22. The method of claim 21, wherein,

2 the plurality of sidewalls provide a diffusion barrier
3 and an etch stop.

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1 23. The method of claim 22, wherein,
2 the plurality of sidewalls protect the first material
3 under the plurality of sidewalls from being etched during the
4 etching of the first material.

1 24. The method of claim 22, wherein,
2 the plurality of sidewalls protect the second material
3 under the plurality of sidewalls from being etched during the
4 etching of the second material.

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1 25. The method of claim 22, wherein,
2 the plurality of sidewalls protect the first material
3 and the second material under the plurality of sidewalls from
4 being etched during the vertical etching of the first
5 material and the second material.

1 26. The method of claim 22, wherein,
2 the plurality of sidewalls protect the first material or
3 the second material under the plurality of sidewalls from
4 being etched during the vertical etching of the first
5 material or the second material.

1 27. A method of processing for a semiconductor device,
2 the method comprising:
3 providing a substrate of the semiconductor device;

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4 forming a plurality of sidewalls above a surface of the
5 substrate;

6 vertically etching horizontal surfaces of a material
7 located around the plurality of sidewalls; and
8 diffusing a dopant around the plurality of sidewalls.

1 28. The method of claim 27, wherein,
2 the plurality of sidewalls are formed by
3 forming a plurality of cylindrical pedestals above
4 a surface of the substrate,
5 depositing a sidewall material layer over the
6 cylindrical pedestals and the substrate,
7 vertically etching the horizontal surfaces of the
8 sidewall material, and
9 etching away the plurality of cylindrical
10 pedestals.

1 29. The method of claim 27, wherein,
2 the vertical etching of horizontal surfaces of the
3 material located around the plurality of sidewalls is
4 performed using a substantially anisotropic etchant.

1 30. The method of claim 27, wherein,
2 the plurality of sidewalls provide an etch stop and a
3 diffusion barrier.

1 31. The method of claim 30, wherein,

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2 the plurality of sidewalls protect the material under
3 the plurality of sidewalls from being etched during the
4 etching of the material around the plurality of sidewalls and
5 the plurality of sidewalls protect the material under the
6 plurality of sidewalls from receiving the dopant during the
7 diffusing of the dopant around the plurality of sidewalls.

1 32. A method of processing for a semiconductor device,
2 the method comprising:
3 providing a substrate of the semiconductor device;
4 forming a plurality of sidewalls above a surface of the
5 substrate; and
6 diffusing a dopant around the plurality of sidewalls.

1 33. The method of claim 32, wherein,
2 the plurality of sidewalls provide a diffusion barrier.

1 34. The method of claim 32, wherein,
2 the plurality of sidewalls are formed by
3 forming a plurality of cylindrical pedestals above
4 a surface of the substrate,
5 depositing a sidewall material layer over the
6 cylindrical pedestals and the substrate,
7 vertically etching the horizontal surfaces of the
8 sidewall material, and
9 etching away the plurality of cylindrical
10 pedestals.

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1 35. The method of claim 32, further comprising:
2 vertically etching horizontal surfaces of a material
3 located around the plurality of sidewalls.

1 36. The method of claim 35, wherein,
2 the plurality of sidewalls provide an etch stop and a
3 diffusion barrier.

1 37. The method of claim 35, wherein,
2 the vertical etching of horizontal surfaces of the
3 material located around the plurality of sidewalls is
4 performed using a substantially anisotropic etchant.

1 38. The method of claim 36, wherein,
2 the plurality of sidewalls protect the material under
3 the plurality of sidewalls from being etched during the
4 vertical etching of horizontal surfaces of the material
5 around the plurality of sidewalls and the plurality of
6 sidewalls protect the material under the plurality of
7 sidewalls from receiving the dopant during the diffusing of
8 the dopant around the plurality of sidewalls.

1 39. The method of claim 35, wherein,
2 the material located around the plurality of sidewalls
3 which is vertically etched is the substrate.

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1 40. The method of claim 35, wherein,
2 the material located around the plurality of sidewalls
3 which is vertically etched is a layer exposed over a surface
4 of the substrate and protected under the plurality of
5 sidewalls.

1 41. A method of processing for a semiconductor device,
2 the method comprising:
3 providing a substrate of the semiconductor device;
4 forming a plurality of sidewalls above a surface of the
5 substrate; and
6 vertically etching horizontal surfaces of a material
7 located around the plurality of sidewalls.

1 42. The method of claim 41, wherein,
2 the plurality of sidewalls provide an etch stop.

1 43. The method of claim 41, wherein,
2 the material located around the plurality of sidewalls
3 which is horizontally etched is the substrate.

1 44. The method of claim 41, wherein,
2 the material located around the plurality of sidewalls
3 which is horizontally etched is an epitaxial layer of the
4 substrate.

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1 45. The method of claim 41, wherein,
2 the material located around the plurality of sidewalls
3 which is horizontally etched is a layer exposed over a
4 surface of the substrate and protected under the plurality of
5 sidewalls.

1 46. The method of claim 41, wherein,
2 the vertical etching of horizontal surfaces of the
3 material located around the plurality of sidewalls is
4 performed using a substantially anisotropic etchant.

1 47. The method of claim 41, wherein,
2 the plurality of sidewalls are formed by
3 forming a plurality of cylindrical pedestals above
4 a surface of the substrate,
5 depositing a sidewall material layer over the
6 cylindrical pedestals and the substrate,
7 vertically etching the horizontal surfaces of the
8 sidewall material, and
9 etching away the plurality of cylindrical
10 pedestals.

1 48. The method of claim 41, further comprising:
2 diffusing a dopant around the plurality of sidewalls.

1 49. The method of claim 48, wherein,

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2 the plurality of sidewalls provide an etch stop and a
3 diffusion barrier.

1 50. The method of claim 49, wherein,
2 the plurality of sidewalls protect the material under
3 the plurality of sidewalls from being etched during the
4 vertical etching of the material located around the plurality
5 of sidewalls and the plurality of sidewalls protect the
6 material under the plurality of sidewalls from receiving the
7 dopant during the diffusing of the dopant around the
8 plurality of sidewalls.

1 51. The method of claim 48, wherein,
2 the dopant is diffused into the substrate around the
3 plurality of sidewalls.

1 52. The method of claim 48, wherein,
2 the dopant is diffused into the material around the
3 plurality of sidewalls.

1 53. A semiconductor device, comprising:
2 a substrate;
3 a plurality of sidewalls above a surface of the
4 substrate;
5 a dopant implanted around the plurality of sidewalls;
6 and

7 wherein the plurality of sidewalls provide a diffusion
8 barrier and protect the dopant from being implanted
9 underneath the plurality of sidewalls.

1 54. The semiconductor device of claim 53, further
2 comprising:

3 a trench etched into the substrate and through a
4 material located on the substrate around the plurality of
5 sidewalls; and

6 wherein the plurality of sidewalls provide an etch stop
7 and protect the substrate and the material underneath the
8 plurality of sidewalls from being etched.

1 55. The semiconductor device of claim 53, further
2 comprising:

3 a trench etched into the substrate around the plurality
4 of sidewalls; and

5 wherein the plurality of sidewalls provide an etch stop
6 and protect the substrate underneath the plurality of
7 sidewalls from being etched.

1 56. A semiconductor device, comprising:

2 a substrate;

3 a plurality of sidewalls above a surface of the
4 substrate;

5 a trench etched around the plurality of sidewalls; and

1 59. The system of claim 58, wherein,
2 the means for etching the material is a gas, plasma, or
3 liquid.

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1 60. The system of claim 58, wherein,
2 the means for etching includes an excitation field to
3 excite ions in a gas, plasma, or liquid.

1 61. The system of claim 58, further comprising:
2 a means for diffusing dopants into a material around the
3 plurality of sidewalls; and
4 wherein the plurality of sidewalls provide a diffusion
5 barrier to protect the material underneath the plurality of
6 sidewalls from being implanted.

1 62. The system of claim 61, wherein,
2 the means for diffusing dopants in the material is a
3 gas, plasma, or liquid.

1 63. The system of claim 58, wherein,
2 the container is a chamber, an oven, or a bath tub.

1 64. A system for manufacturing a semiconductor device
2 comprising:
3 a container for receiving a semiconductor wafer;
4 the semiconductor wafer having a plurality of sidewalls
5 formed over a substrate;
6 a means for diffusing a dopant into a material around
7 the plurality of sidewalls; and

8 wherein the plurality of sidewalls provide a diffusion
9 barrier to protect the material underneath the plurality of
10 sidewalls from being implanted.

1 65. The system of claim 64, wherein,
2 the means for diffusing dopants into the material is a
3 gas, plasma, or liquid.

1 66. The system of claim 64, wherein,
2 the means for diffusing includes an excitation field to
3 implant the dopant into the material around the plurality of
4 sidewalls.

1 67. The system of claim 64, wherein,
2 the means for diffusing includes a source of heat to
3 diffuse the dopant into the material around the plurality of
4 sidewalls.

1 68. The system of claim 64, wherein,
2 the source of heat is an oven.

1 69. The system of claim 64, further comprising:
2 a means for etching into a material around the plurality
3 of sidewalls; and
4 wherein the plurality of sidewalls provide an etch stop
5 to protect the material underneath the plurality of sidewalls
6 from being etched.

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1 70. The system of claim 69, wherein,
2 the means for etching the material is a gas, plasma, or
3 liquid.

1 71. The system of claim 70, wherein,
2 the means for etching includes an excitation field to
3 excite ions in a gas, plasma, or liquid.

1 72. The system of claim 71, wherein,
2 the container is a chamber, an oven, or a bath tub.

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